

2SD1113(K)

Silicon NPN Triple Diffused

HITACHI

ADE-208-903 (Z)

1st. Edition

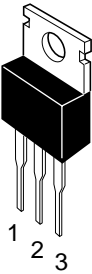
Sep. 2000

Application

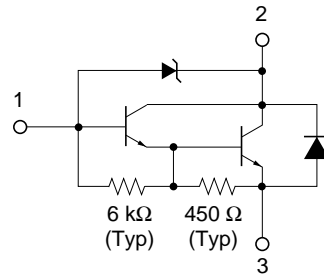
Igniter

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter



Absolute Maximum Ratings (T_a = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	6	A
Collector peak current	I _{C(peak)}	10	A
Collector power dissipation	P _C ^{*1}	40	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

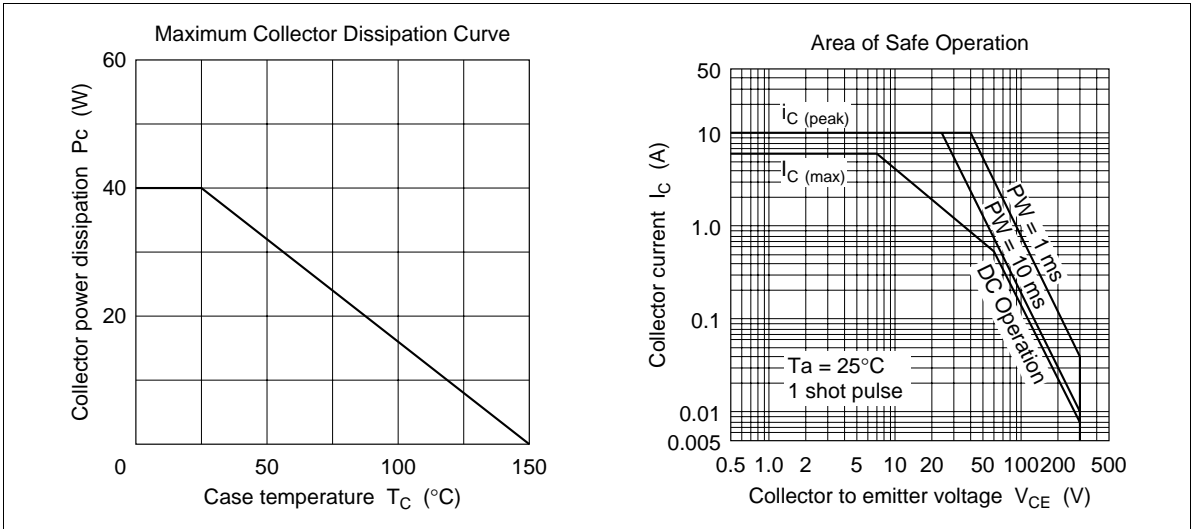
Note: 1. Value at T_C = 25°C.

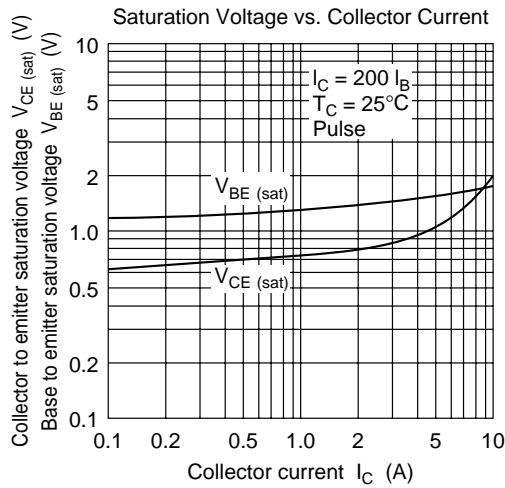
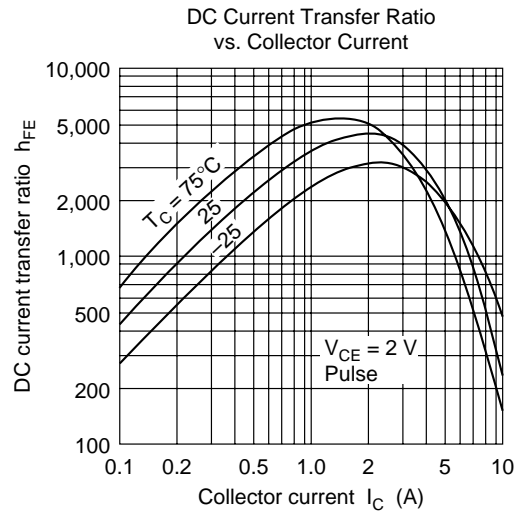
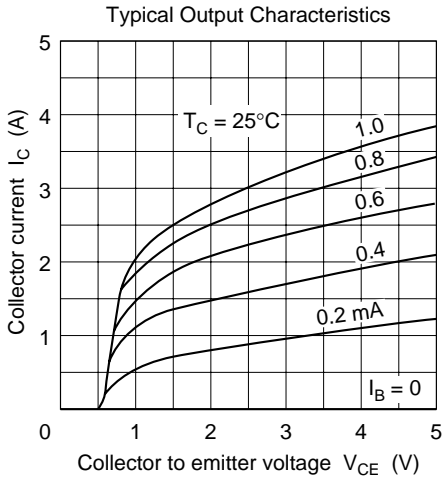
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Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	500	V	$I_C = 0.1 \text{ mA}, I_E = 0$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	300	—	—	V	$I_C = 3 \text{ A}, PW = 50 \mu\text{s}, f = 50 \text{ Hz}, L = 10 \text{ mH}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CEO}	—	—	100	μA	$V_{CE} = 300 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE}	500	—	—		$V_{CE} = 2 \text{ V}, I_C = 4 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 4 \text{ A}, I_B = 40 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 4 \text{ A}, I_B = 40 \text{ mA}^{*1}$
Turn on time	t_{on}	—	2.0	—	μs	$I_C = 4 \text{ A}, I_{B1} = -I_{B2} = 40 \text{ mA}$
Turn off time	t_{off}	—	23	—	μs	$I_C = 4 \text{ A}, I_{B1} = -I_{B2} = 40 \text{ mA}$

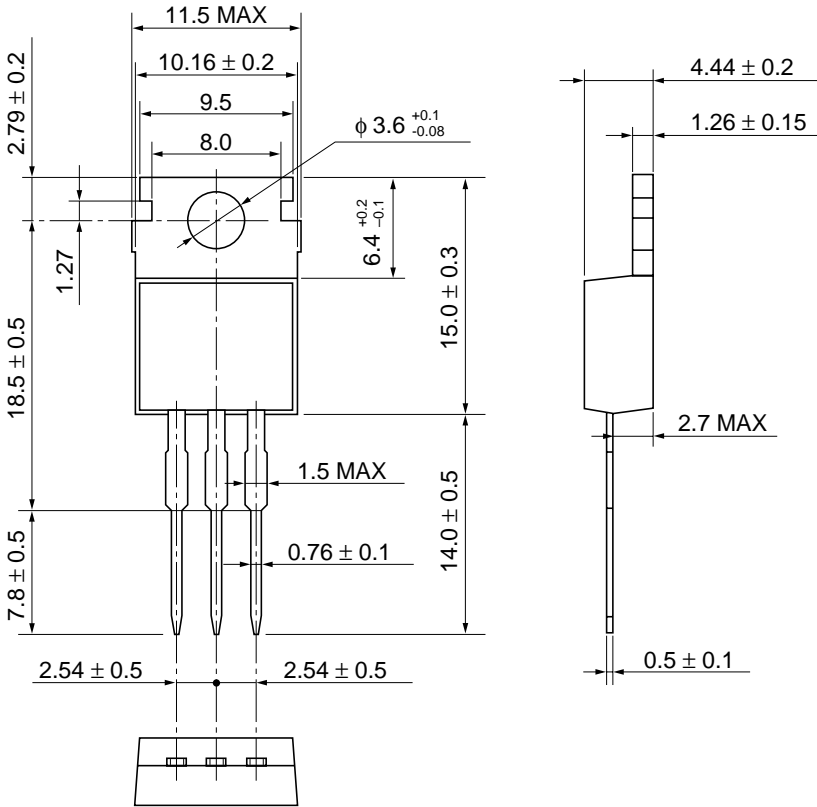
Note: 1. Pulse test.





Package Dimensions

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

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